IN THE CLAIMS:

Please amend claims 1 and 9 and add new claim 19 as follows:

LISTING OF CURRENT CLAIMS

Claim 1 (Currently Amended). A light emitting diode comprising:

a light emitting structure having a plurality of light emitting layers which generate light in responsive to an injection current;

a transparent conductive oxide layer formed on said light emitting structure;

a metal reflective layer formed on said transparent conductive oxide layer, said transparent conductive oxide layer being formed to prevent said metal reflective layer from reacting with said light emitting layers while annealing for improving ohmic contact of electrodes of said light emitting diode; and

a conductive base substrate formed on said metal reflective layer.

Claim 2. (Original) The light emitting diode according to claim 1, wherein said conductive base structure is selected from the group consisting of copper, aluminum, SiC, AlN and silicon.

Claim 3. (Original) The light emitting diode according to claim 1, wherein the transparent conductive oxide layer is selected from the group consisting In_2O_3, SnO_2, CdO, ZnO, ITO, CTO, $CuAlO_2$, $CuGaO_2$ and $SrCu_2O_2$.

Claim 4. (Original) The light emitting diode according to claim 1, wherein said metal reflective layer is selected from the group consisting of Au, Al and Ag.

Claim 5. (Original) The light emitting diode according to claim 1, further comprising a metal bonding layer formed in between said conductive base substrate and said metal reflective layer.

Claim 6. (Original) The light emitting diode according to claim 5, wherein said bonding layer is selected from the group consisting of In, Au-Sn alloy, Au-Si alloy, Pb-Sn alloy and Au-Ge alloy, PdIn.

Claim 7. (Original) The light emitting diode according to claim 5, further comprising a diffusion barrier layer formed in between said metal reflective layer and said metal bonding layer.

Claim 8. (Original) The light emitting diode according to claim 7, wherein said diffusion barrier layer is selected from the group consisting of conductive oxide layer, refractory metal layer, and refractory metal silicide.

Claim 9. (Currently Amended) A light emitting diode comprising:

a conductive base substrate;

a light emitting structure having a plurality of light emitting layers which generate light in responsive to an injection current;

a transparent conductive oxide layer formed on said light emitting structure;

a metal reflective layer formed on said transparent conductive oxide layer, said transparent conductive oxide layer being formed to prevent said metal reflective layer from reacting with said light emitting layers while annealing for improving ohmic contact of electrodes of said light emitting diode; and

a metal bonding layer formed in between said conductive base substrate and said metal reflective layer so as to bond said conductive base substrate and said light emitting structure.

Claim 10. (Original) The light emitting diode according to claim 9, wherein said conductive base substrate is a heat dissipation and elextrixal conductive layer selected from the group consisting of copper, aluminum, SiC, AlN and silicon.

Claim 11. (Original) The light emitting diode according to claim 9, wherein said transparent conductive layer is selected from the group consisting of In_2O_3, SnO_2, CdO, ZnO, ITO, CTO, $CuAlO_2$, $CuGaO_2$ and $SrCu_2O_2$.

Claim 12. (Original) The light emitting diode according to claim 9, wherein said metal reflective layer is selected from the group consisting of Au, Al and Ag.

Claim 13. (Original) The light emitting diode according to claim 9, wherein said metal bonding layer is selected from the group consisting of In, Au-Sn alloy, Au-Si alloy, Pb-Sn alloy and Au-Ge alloy, PdIn.

Claim 14. (Original) The light emitting diode according to claim 13, further comprising a diffusion barrier layer formed in between said metal reflective layer and said metal bonding layer.

Claim 15. (Original) The light emitting diode according to claim 14, wherein said diffusion barrier layer is selected from the group consisting of conductive oxide layer, refractory metal layer, and refractory metal silicide.

Claims 16-18 (Previously Withdrawn).

Claim 19. (New) The light emitting diode according to claim 9, wherein said transparent conductive oxide layer has an ohmic contact metal pattern layer formed therein.